NSN 5961-01-047-2519

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-047-2519 **Inclosure Material:** Ceramic **Overall Length:** 0.290 inches **Overall Height:** 0.090 inches **Overall Width:** 1.000 inches **Component Name And Quantity:** 8 semiconductor device diode **Mounting Method: Terminal Semiconductor Material:** Silicon all semiconductor device diode Voltage Rating In Volts Per Characteristic: 60.0 reverse breakdown voltage, dc all semiconductor **Current Rating Per Characteristic:** 300.00 milliamperes forward current, average absolute all semiconductor device diode and 500.00 milliamperes forward current, average preset all semiconductor device diode **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector preset all semiconductor device diode **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Precious Material And Location:** Terminal surface option gold **Precious Material:** Gold **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 10 pin **Specification Data:** 81349-mil-s-19500/474 government specification Shelf Life: N/a **Unit Of Measure:**

Fiig: A110a0

No

Demilitarization: